

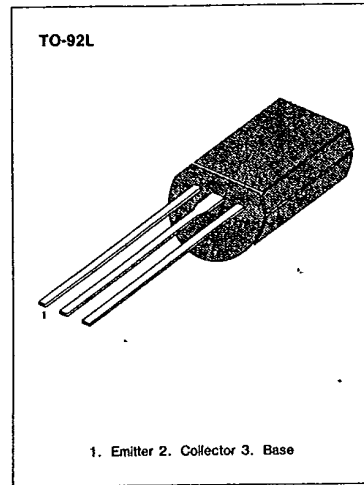
**KSC2383**

**NPN EPITAXIAL SILICON TRANSISTOR**

COLOR TV AUDIO OUTPUT  
 COLOR TV VERTICAL DEFLECTION OUTPUT

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	160	V
Collector-Emitter Voltage	V <sub>CE0</sub>	160	V
Emitter-Base Voltage	V <sub>EB0</sub>	6	V
Collector Current	I <sub>C</sub>	1	A
Base Current	I <sub>B</sub>	0.5	A
Collector Dissipation	P <sub>C</sub>	900	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)**

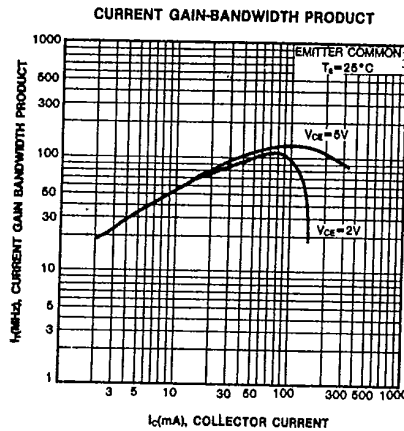
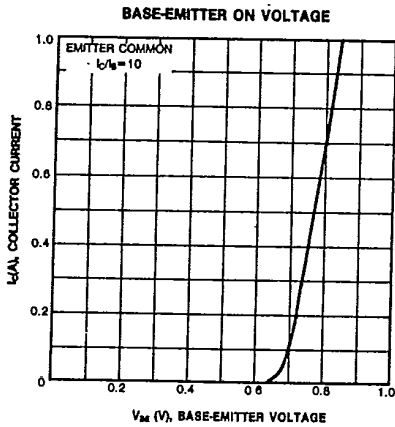
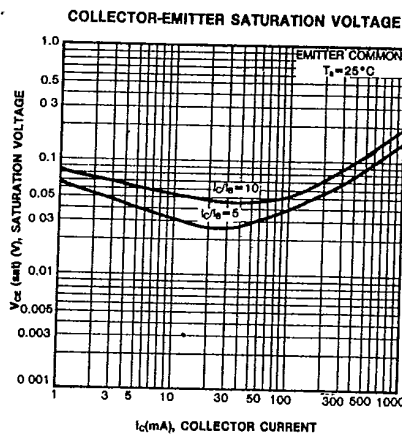
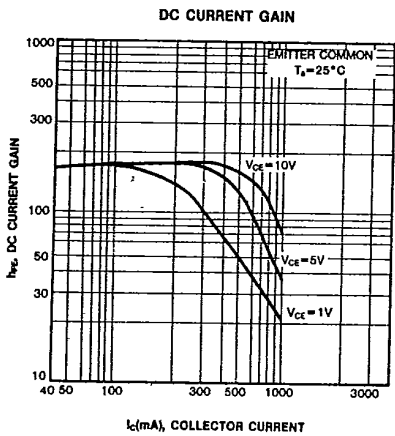
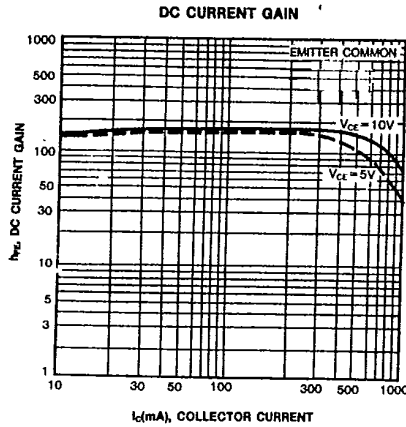
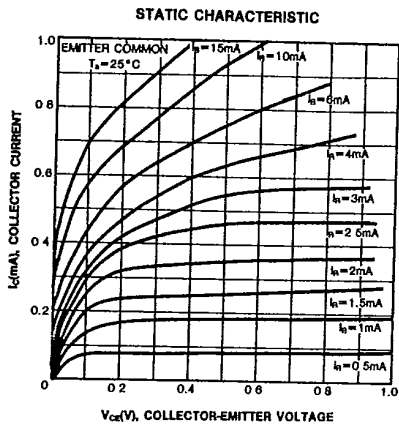
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =150V, I <sub>E</sub> =0			1	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =6V, I <sub>C</sub> =0			1	μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	.160			V
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =200mA	60		320	
Collector-Emitter Saturation Voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1.5	V
Base Emitter On Voltage	V <sub>BE (on)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =5mA	0.45		0.75	V
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =200mA	20	100		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			20	pF

**h<sub>FE</sub> CLASSIFICATION**

Classification	R	O	Y
h <sub>FE</sub>	60-120	100-200	160-320

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3

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